CHENMKO ENTERPRISE CO.,LTD

BAW56N1PT

SURFACE MOUNT
SWITCHING DIODE
VOLTAGE 85 Volts CURRENT 0.15 Ampere

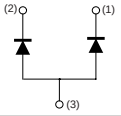
Lead free devices

APPLICATION
* Ultra high speed switching

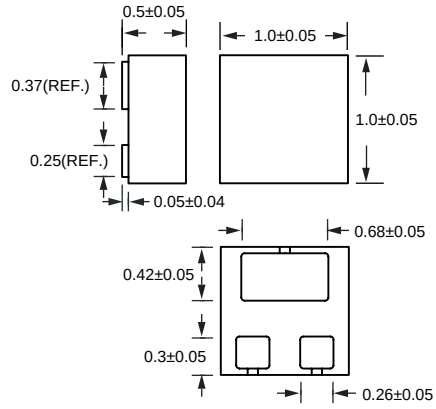
FEATURE
* Small surface mounting type. (FBPT-923)
* High speed. (T_{RR}=1.5nSec Typ.)
* Suitable for high packing density.
* Peak forward current is 450mA.

CONSTRUCTION
* Silicon epitaxial planar

CIRCUIT



FBPT-923



Dimensions in millimeters

FBPT-923

MAXIMUM RATINGES (At T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	BAW56N1PT	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	85	Volts
Maximum RMS Voltage	V_{RMS}	60	Volts
Maximum DC Blocking Voltage	V_{DC}	70	Volts
Maximum Average Forward Rectified Current	I_O	0.15	Amps
Peak Forward Surge Current at 1uSec.	I_{FSM}	4.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	C_J	2.0	pF
Maximum Reverse Recovery Time (Note 2)	T_{RR}	4.0	nSec
Maximum Operating Temperature Range	T_J	+150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (At T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	BAW56N1PT	UNITS
Maximum Instantaneous Forward Voltage at I_F= 150mA	V_F	1.25	Volts
Maximum Average Reverse Current at V_R= 75V	I_R	1.0	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0 volts.
2. Measured at applied froward current of 10mA and reverse voltage of 10.0 volts.
3. ESD sensitive product handling required.

RATING CHARACTERISTIC CURVES (BAW56N1PT)

FIG. 1 - TYPICAL FORWARD CURRENT DERAING CURVE

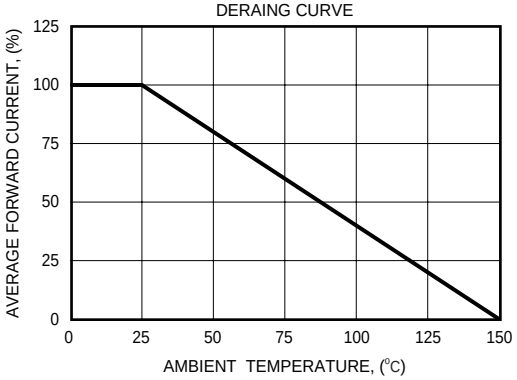


FIG. 2 - FORWARD CHARACTERISTICS

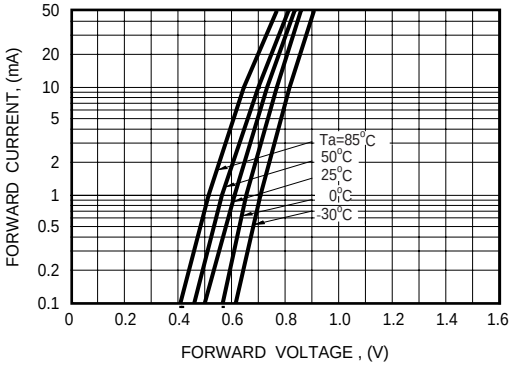


FIG. 3 - REVERSE CHARACTERISTICS

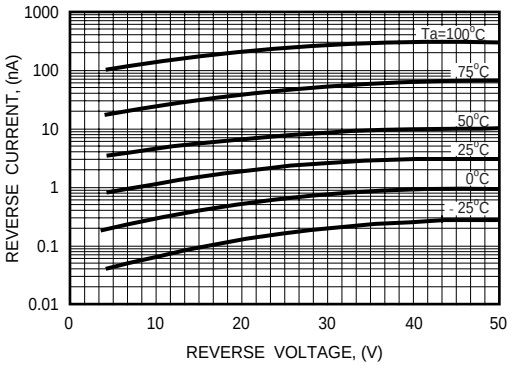


FIG. 4 - TYPICAL JUNCTION CAPACITANCE

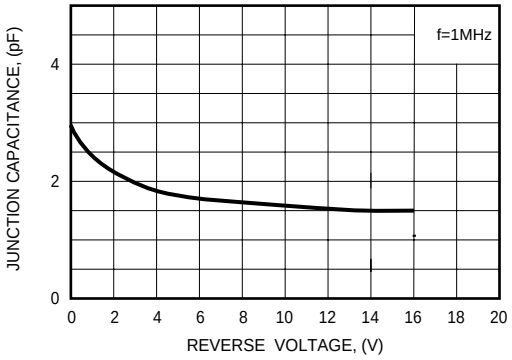


FIG. 5 - REVERSE RECOVERY TIME

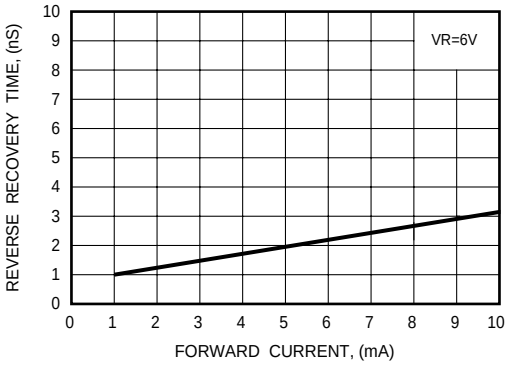


FIG. 6 - REVERSE RECOVERY TIME MEASUREMENT CIRCUIT

